

ABSTRACT OF THE DISCLOSURE

A semiconductor device comprises a first insulating film formed over a semiconductor substrate, a second insulating film formed on the first insulating film, a contact plug made of a conductive material vertically penetrating the first and second insulating films and extending on the second insulating film, and a conductor film in contact with the upper surface of the contact plug and part of the second insulating film. This construction makes it possible to form minute via-holes in a mass-production line without increasing parasitic capacity, increasing the number of manufacturing steps, and generating defects.